



## 1. Product profile

### **1.1 General description**

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (DPAK) surface mounted package.

### **1.2 Features and benefits**

- Fast switching
- High voltage capability

### **1.3 Applications**

- DC-to-DC converters
- High-frequency electronic lighting ballast applications
- Low thermal resistance
- Surface-mountable package
- Inverters
- Motor control systems

### **1.4 Quick reference data**

#### Table 1. Quick reference data

Parameter					
	Conditions	Min	Тур	Max	Unit
collector current	see Figure 1; see Figure 2; see Figure 4	-	-	4	A
total power dissipation	T <sub>mb</sub> ≤ 25 °C; see <u>Figure 3</u>	-	-	80	W
collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	1050	V
racteristics					
DC current gain	I <sub>C</sub> = 0.1 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 11</u>	<u>[1]</u> 48	66	100	
	$I_{C} = 0.8 \text{ A}; V_{CE} = 3 \text{ V};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{12}$	[1] 25	42	50	
	total power dissipation collector-emitter peak voltage	$see \frac{Figure 4}{Figure 4}$ total power dissipation $T_{mb} \le 25 \text{ °C}$ ; see $Figure 3$ collector-emitter peak $V_{BE} = 0 \text{ V}$ voltage $DC \text{ current gain} \qquad I_{C} = 0.1 \text{ A}; \text{ V}_{CE} = 5 \text{ V};$ $T_{mb} = 25 \text{ °C}; \text{ see } Figure 11$ $I_{C} = 0.8 \text{ A}; \text{ V}_{CE} = 3 \text{ V};$	see Figure 4total power dissipation $T_{mb} \le 25 \text{ °C}$ ; see Figure 3-collector-emitter peak voltage $V_{BE} = 0 \text{ V}$ -racteristicsDC current gain $I_C = 0.1 \text{ A}; \text{ V}_{CE} = 5 \text{ V};$ $T_{mb} = 25 \text{ °C}; see Figure 11}$ 11 $I_C = 0.8 \text{ A}; \text{ V}_{CE} = 3 \text{ V};$ 1125	$see \frac{Figure 4}{see Figure 3}$ $collector-emitter peak voltage V_{BE} = 0 V$ $racteristics$ $DC current gain \begin{cases} I_C = 0.1 \text{ A}; V_{CE} = 5 \text{ V}; \\ T_{mb} = 25 \text{ °C}; see \frac{Figure 11}{see Figure 11} \end{cases}$ $I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; \qquad [1] 25  42$	$see \frac{Figure 4}{Figure 4}$ total power dissipation $T_{mb} \le 25 \text{ °C}$ ; see $Figure 3$ 80 collector-emitter peak $V_{BE} = 0 \text{ V}$ 1050 voltage $Tacteristics$ $DC \text{ current gain} \qquad I_C = 0.1 \text{ A}; V_{CE} = 5 \text{ V}; \qquad \begin{array}{c} 11 \\ T_{mb} = 25 \text{ °C}; \text{ see } Figure 11 \\ \hline I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; \qquad \begin{array}{c} 11 \\ 125 \\ 50 \end{array}$

[1] Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %



## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		_
2	С	collector <sup>[1]</sup>	mb	C
3	E	emitter		вК
mb	С	mounting base; connected to collector		E sym123
			SOT428 (DPAK)	

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

## 3. Ordering information

Table 3. Order	ing information		
Type number	Package		
	Name	Description	Version
BUJ302AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

## 4. Limiting values

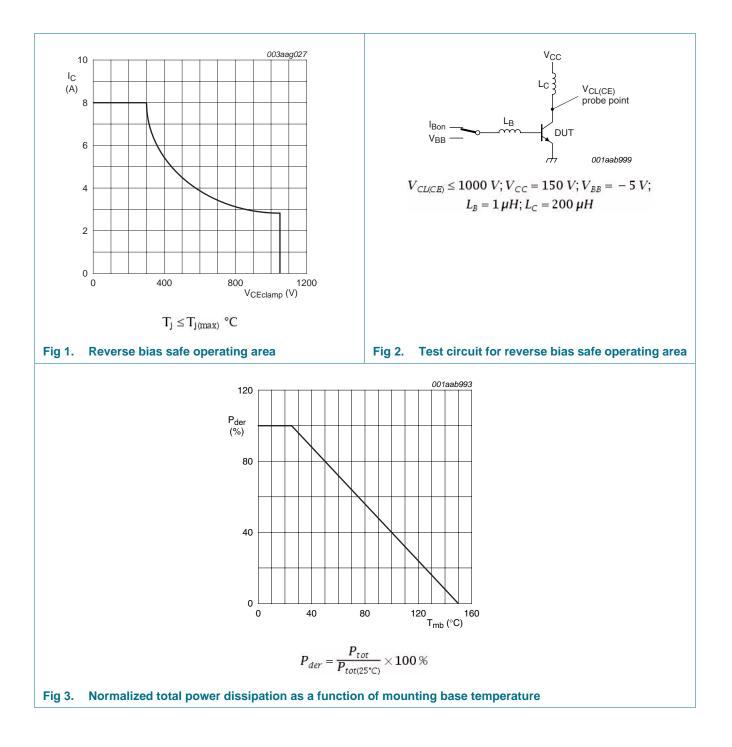
#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	1050	V
V <sub>CEO</sub>	collector-emitter voltage	$I_{B} = 0 A$	-	400	V
I <sub>C</sub>	collector current	see <u>Figure 1;</u> see <u>Figure 2</u> ; see <u>Figure 4</u>	-	4	А
I <sub>CM</sub>	peak collector current		-	8	А
I <sub>B</sub>	base current		-	2	А
I <sub>BM</sub>	peak base current		-	4	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; see <u>Figure 3</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V <sub>EBO</sub>	emitter-base voltage	$I_{C} = 0 \text{ A}; I_{E} = 2 \text{ A}; t_{p} < 10 \text{ ms}$	-	24	V
-					

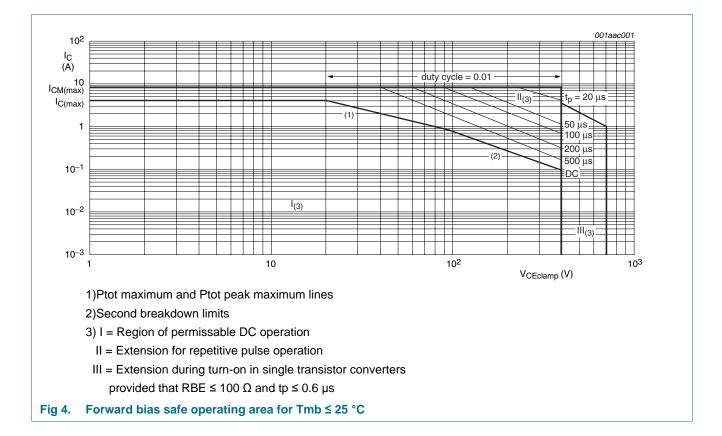
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### **NPN** power transistor



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**NPN** power transistor

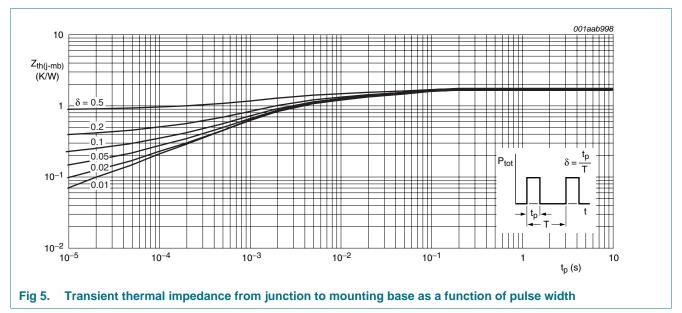


BUJ302AD

4 of 14

## 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 5	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to amb	pient in free air	-	60	-	K/W

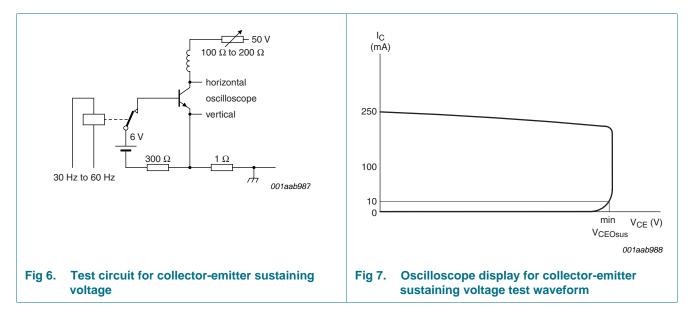


# Table 5. Thermal characteristics

## 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
I <sub>CES</sub>	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 1050 \text{ V}; T_{mb} = 25 \text{ °C}$		-	0.2	10	μA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE}$ = 400 V; I <sub>B</sub> = 0 A; T <sub>mb</sub> = 25 °C		-	10	250	mA
V <sub>(BR)EBO</sub>	open-collector emitter-base breakdown voltage	$I_B = 1 \text{ mA}; I_C = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		15	19	-	V
V <sub>CEOsus</sub>	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 10 \text{ mA}; L_C = 25 \text{ mH};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{Figure 7}};$ see $\frac{\text{Figure 7}}{100000000000000000000000000000000000$	<u>[1]</u>	400	470	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = 1 \text{ A}; I_{B} = 0.2 \text{ A}; T_{mb} = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	[1]	-	0.15	0.5	V
		$I_{C} = 3.5 \text{ A}; I_{B} = 1 \text{ A}; T_{mb} = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	<u>[1]</u>	-	0.6	1.5	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 3.5 A; I <sub>B</sub> = 1 A; T <sub>mb</sub> = 25 °C; see <u>Figure 10</u>	<u>[1]</u>	-	1.1	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.1 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 11</u>	[1]	48	66	100	
		$I_C$ = 0.8 A; $V_{CE}$ = 3 V; $T_{mb}$ = 25 °C; see <u>Figure 12</u>	<u>[1]</u>	25	42	50	
Dynamic	characteristics						
t <sub>s</sub>	storage time	$I_{C}$ = 2.5 A; $I_{Bon}$ = 0.5 A; $I_{Boff}$ = -0.5 A;		-	-	3.5	μs
t <sub>f</sub>	fall time	$R_L = 60 \Omega$ ; $V_{BB} = -5 V$ ; $T_{mb} = 25 °C$ ; resistive load; $t_p = 300 µs$ ; see <u>Figure 13</u> ; see <u>Figure 14</u>		-	-	500	ns

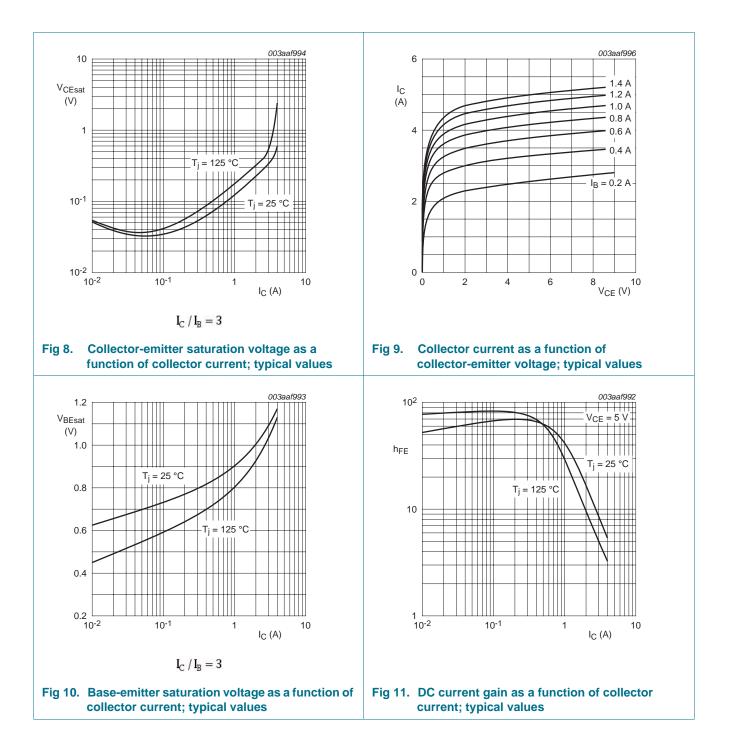
[1] Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %



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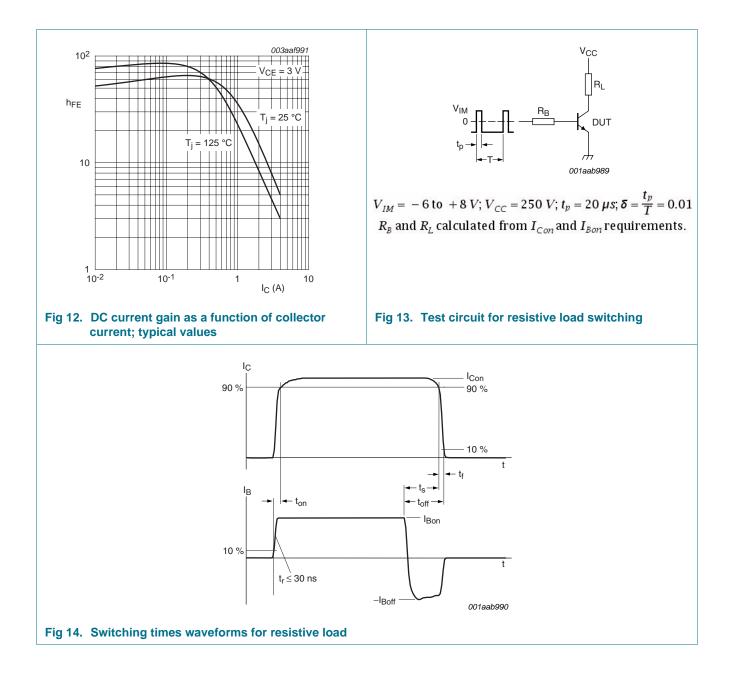
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### **NPN** power transistor



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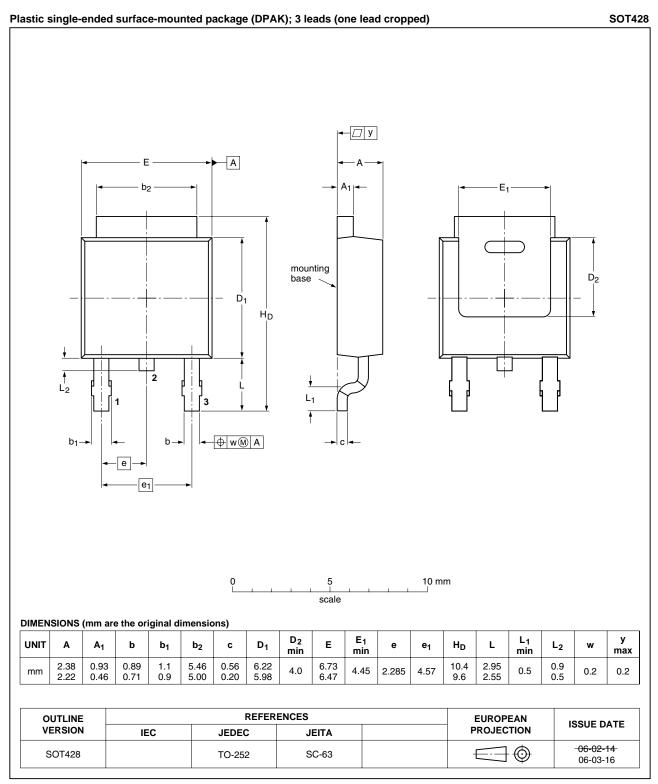
**NPN** power transistor



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**NPN** power transistor

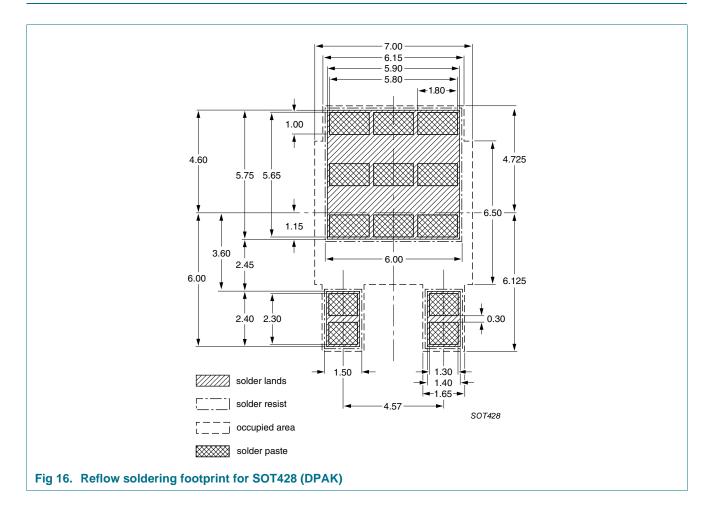
## 7. Package outline



### Fig 15. Package outline SOT428 (DPAK)

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## 8. Soldering



## 9. Revision history

Table 7. Rev	vision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ302AD v.1	20110328	Product data sheet	-	-

### **10. Legal information**

### **10.1** Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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12 of 14

# BUJ302AD

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### **12. Contents**

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics5
6	Characteristics6
7	Package outline9
8	Soldering10
9	Revision history11
10	Legal information12
10.1	Data sheet status
10.2	Definitions12
10.3	Disclaimers
10.4	Trademarks
11	Contact information13

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